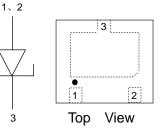


PTVSHC3N15VUL1 Transient Voltage Suppressor

Description

The PTVSHC3N15VUL1 ESD protector is designed to replace multilayer variators (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC3N15VUL1 protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC3N15VUL1 is available in a DFN2×2-3L package with working voltages of 15 volt. It is used to meet the ESD immunity requirements of IEC 61000-4-2 (±30kV air, ±30kV contact discharge)



Feature

- 3400W Peak pulse power per line (t_P = 8/20µs)
- DFN2×2-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
 ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 80A (5/50ns),
 IEC 61000-4-5 (Lightning) 110A (8/20us)

Applications

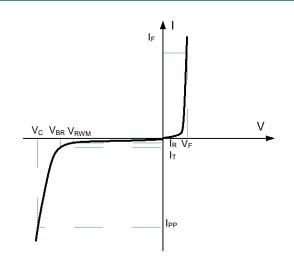
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
 - Peripherals
 - MP3 players

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
Ι _Τ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
CJ	Junction Capacitance	
lF	Forward Current	
V _F	Forward Voltage @ I _F	



Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				15	V
Breakdown Voltage	V _{BR}	I _t =1mA	16	18	20	V
Reverse Leakage Current	I _R	V _{RWM} =15V			1	μA
Clamping Voltage	Vc	I _{PP} =30A t _P = 8/20μs		22	24	V
Clamping Voltage	Vc	I _{PP} =100A t _P = 8/20μs		30	34	V
Peak Pulse Power (t _P = 8/20µS)	P _{pp}		3400			W
Junction Capacitance	Cj	$V_R=0V$ f = 1MHz		500	650	pF

Notes : Measured from pin 3 to pin 1 and pin 2.

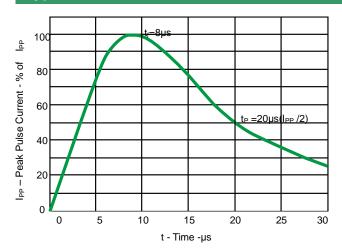
Absolute maximum rating@25℃

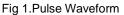
Rating	Symbol	Value	Units
Lead Soldering Temperature	TL	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

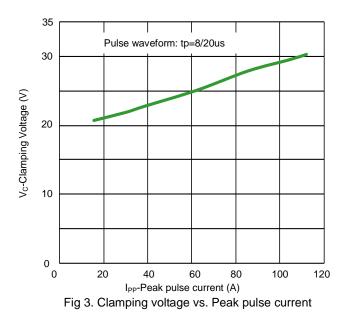
PTVSHC3N15VUL1

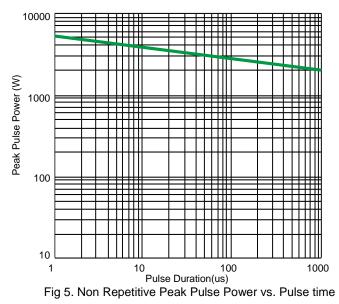
PTVSHC3N15VUL1

Typical Characteristics









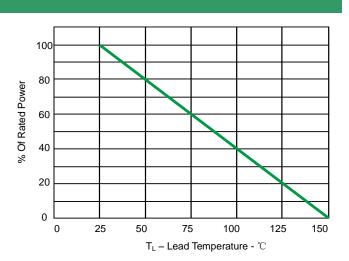
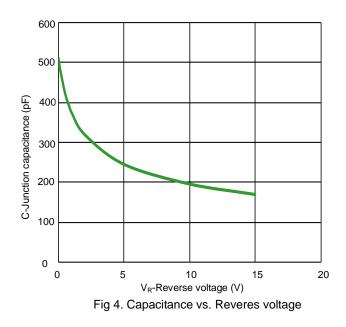
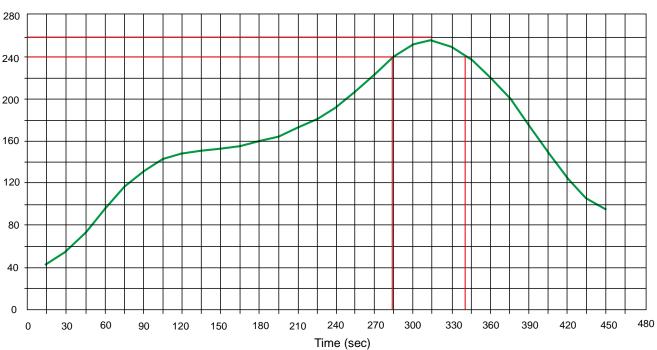


Fig 2.Power Derating Curve



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Solder Reflow Recommendation



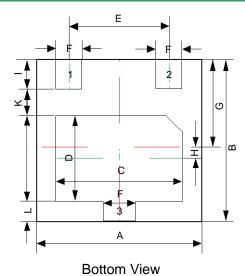
Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

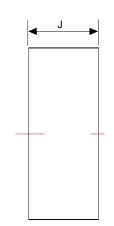
PCB Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

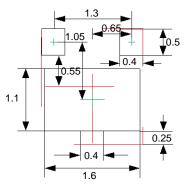
- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN2×2-3L)





Dim	Millimeters		
DIM	MIN	МАХ	
A	1.90	2.10	
В	1.90	2.10	
С	1.40	1.60	
D	0.90	1.10	
E	1.30BSC		
F	0.25	0.35	
G	0.95	1.05	
н	0.20	0.30	
I	0.35	0.45	
J		0.65	
К	0.30	0.35	
L	0.15	0.20	



Unit:mm

Recommended Soldering Pad

Ordering information

Device	Package	Shipping
PTVSHC3N15VUL1	DFN2×2-3L (Pb-Free)	3000 / Tape & Reel

Rev.06.0

PTVSHC3N15VUL1

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